



Features

- Drain-Source Breakdown Voltage V_{DSS} - 50 V
- Drain-Source On-Resistance
 $R_{DS(ON)} 2\Omega$, at $V_{GS} = -10V$, $I_{DS} = -100mA$
 $R_{DS(ON)} 2\Omega$, at $V_{GS} = -5.0V$, $I_{DS} = -100mA$
- Continuous Drain Current at $T_A=25^\circ C$ $I_D = -160mA$
- Advanced high cell density Trench Technology
- RoHS Compliance & Halogen Free

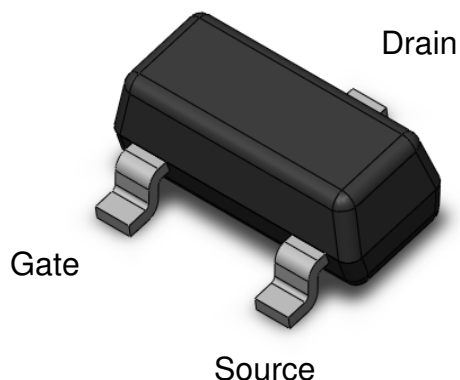
Description

The CTLM16PS05-R3 uses high performance Trench Technology to provide excellent $R_{DS(ON)}$ and low gate charge which is suitable for most of the synchronous buck converter applications .

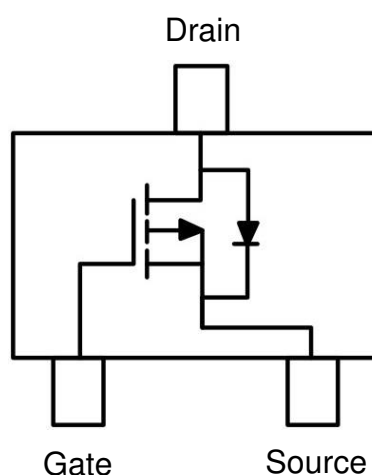
Applications

- Power Management
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch

Package Outline



Schematic



**Absolute Maximum Rating at 25°C**

Symbol	Parameters	Ratings	Units	Notes
V_{DS}	Drain-Source Voltage	-50	V	
V_{GS}	Gate-Source Voltage	±20	V	
I_D	Continuous Drain Current @ $T_A=25^\circ\text{C}$	-0.16	A	1
I_{DM}	Pulsed Drain Current	-0.64	A	1
P_D	Total Power Dissipation @ $T_A=25^\circ\text{C}$	0.22	W	2
T_{STG}	Storage Temperature Range	-55 to 150	°C	
T_J	Operating Junction Temperature Range	-55 to 150	°C	

Thermal Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$R_{\theta JA}$	Thermal Resistance Junction-Ambient (t=10s)		-	555	-	°C /W	1,4



Electrical Characteristics $T_A = 25^\circ\text{C}$ (unless otherwise specified)

Static Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
B _{VDS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-50	-	-	V	
I _{DSS}	Drain-Source Leakage Current	V _{DS} = -50V, V _{GS} = 0V	-	-	-1	μA	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA	

On Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
R _{DS(ON)}	Drain-Source On-Resistance	V _{GS} = -10V, I _D = -100mA	-	2	5		Fig 4
		V _{GS} = -5V, I _D = -100mA	-	2	6		
V _{GS(TH)}	Gate-Source Threshold Voltage	V _{GS} = V _{DS} , I _D = -250μA	-0.8	-	-2.0	V	Fig 5

Dynamic Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
C _{ISS}	Input Capacitance	V _{DS} = -5V , V _{GS} = 0V, f=1MHz	-	41.5	-	pF	Fig 3
C _{OSS}	Output Capacitance		-	19.5	-		
C _{RSS}	Reverse Transfer Capacitance		-	4	-		

Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
T _{D(ON)}	Turn-On Delay Time	V _{DS} = -15V , R _L = 50Ω , V _{GS} = -10V , R _G = 25Ω,	-	13.7	-	ns	Fig 11 & 12
T _R	Rise Time		-	6.2	-		
T _{D(OFF)}	Turn-Off Delay Time		-	15.9	-		
T _F	Fall Time		-	2.8	-		
Q _G	Total Gate Charge	V _{DS} = -40V , . V _{GS} = -4.5V, I _D = -0.5A	-	2.3	-	nC	Fig 9 & 10
Q _{GS}	Gate-Source Charge		-	2.4	-		
Q _{GD}	Gate-Drain (Miller) Charge		-	0.7	-		



CTLM16PS05-R3

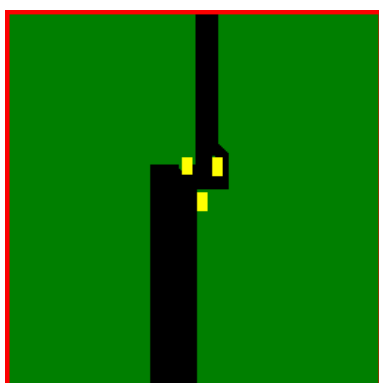
P-Channel Enhancement MOSFET

Drain-Source Diode Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _D = -0.1A			-2.9	V	
I _{SD}	Body Diode Continuous Current				-0.1	A	1

Note:

1. The power dissipation is limited by 150°C junction temperature.
2. Device mounted on a glass-epoxy board



FR-4
25.4 × 25.4 mm .
2 Oz Copper

Actual Size

3. The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
4. Thermal Resistance follow JESD51-3.



Typical Characteristic Curves

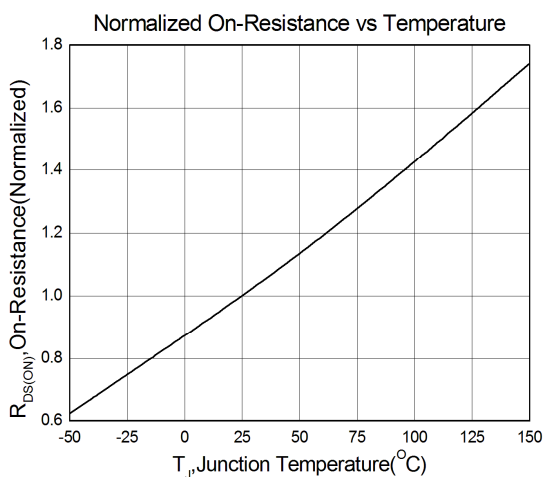


Figure 1

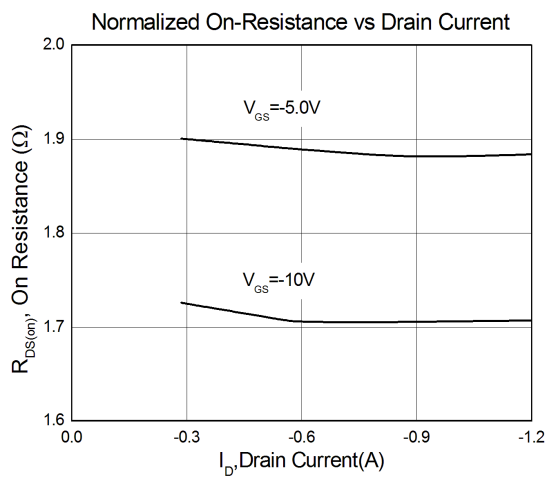


Figure 2

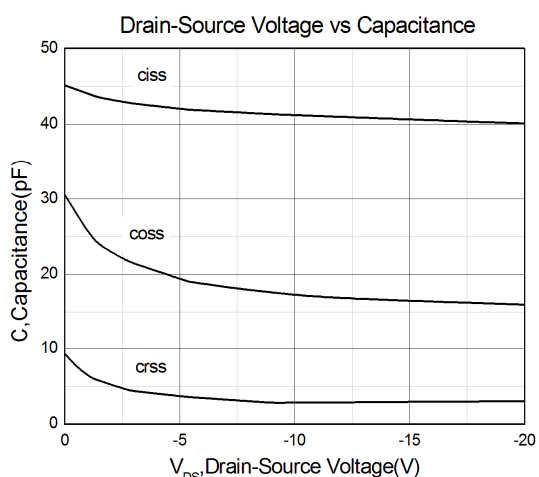


Figure 3

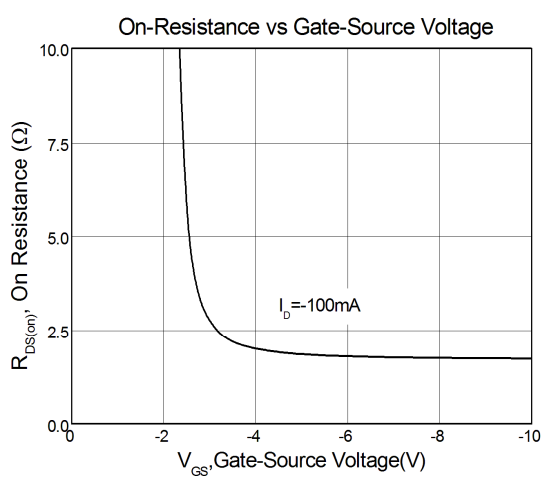


Figure 4

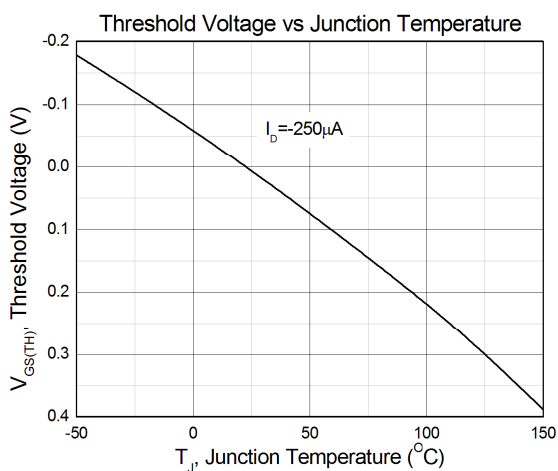


Figure 5

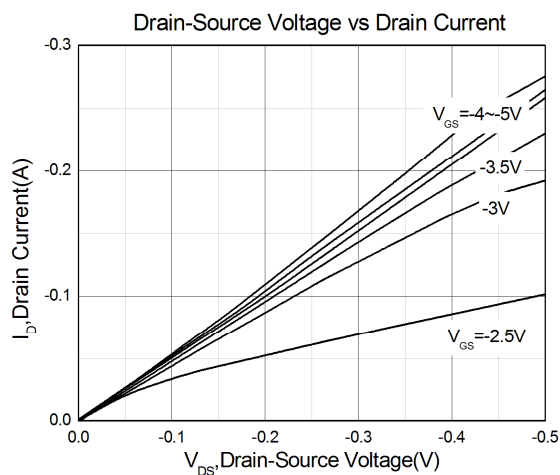


Figure 6

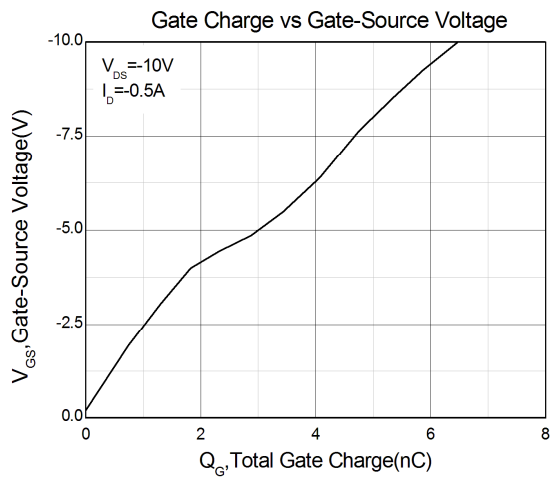


Figure 7

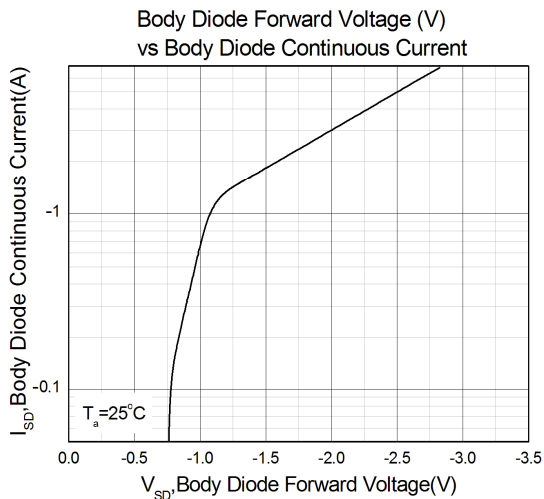


Figure 8



Test Circuits & Waveforms

Figure 9: Gate Charge Test Circuit

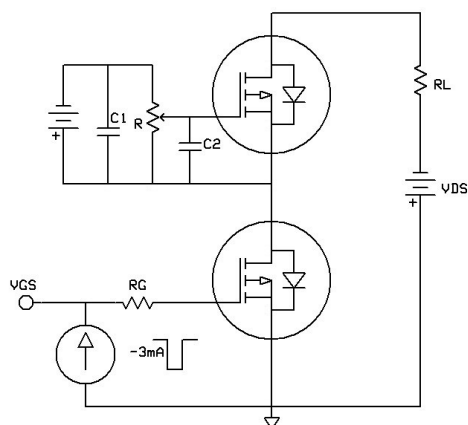


Figure 10: Gate Charge Waveform

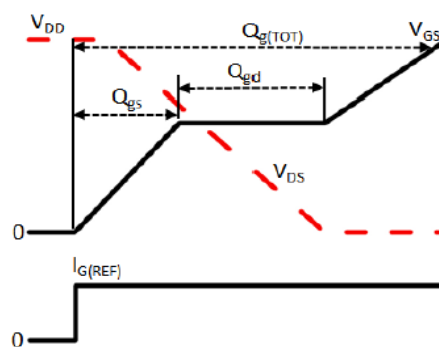


Figure 11: Switching Time Test Circuit

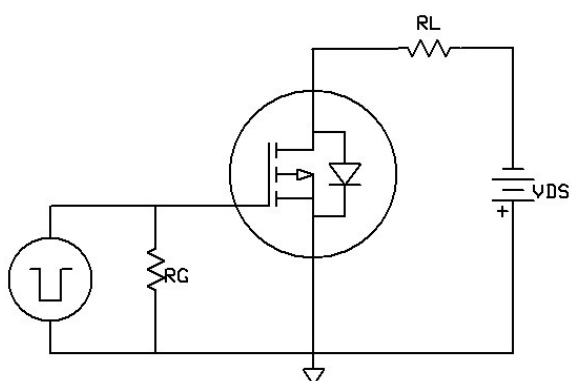
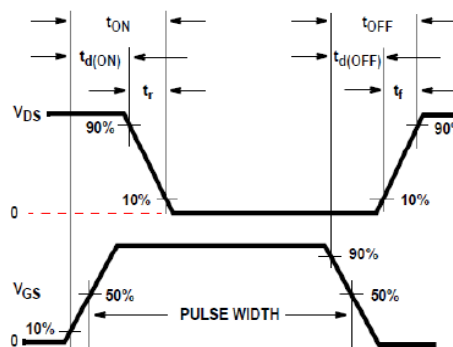
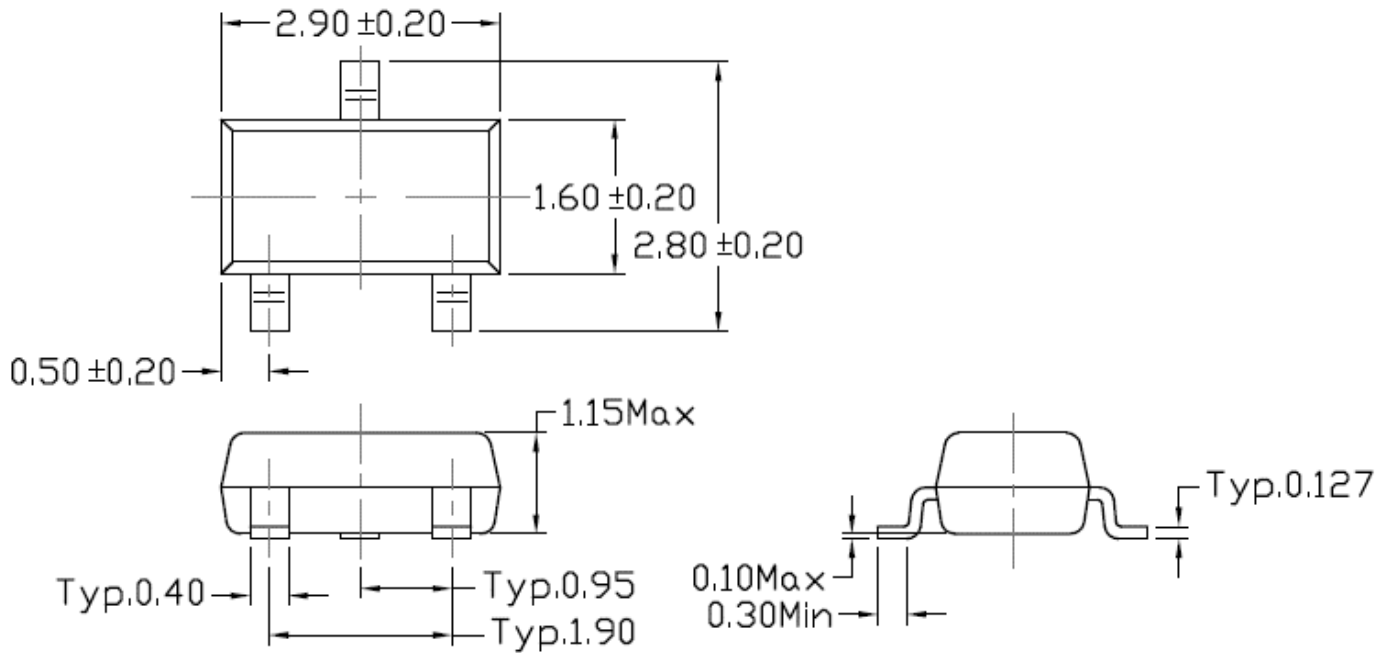


Figure 12: Switching Time Waveform

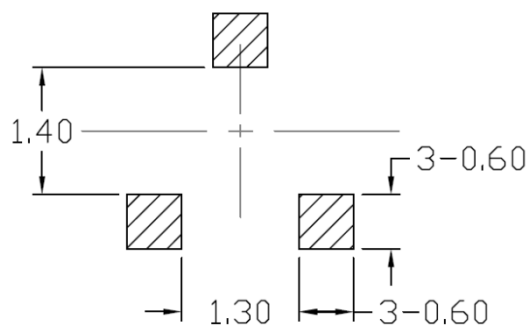




Package Dimension (SC-59)



Recommended pad layout for surface mount leadform

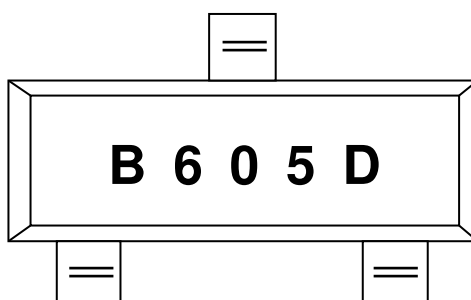




CTLM16PS05-R3

P-Channel Enhancement MOSFET

Marking Information



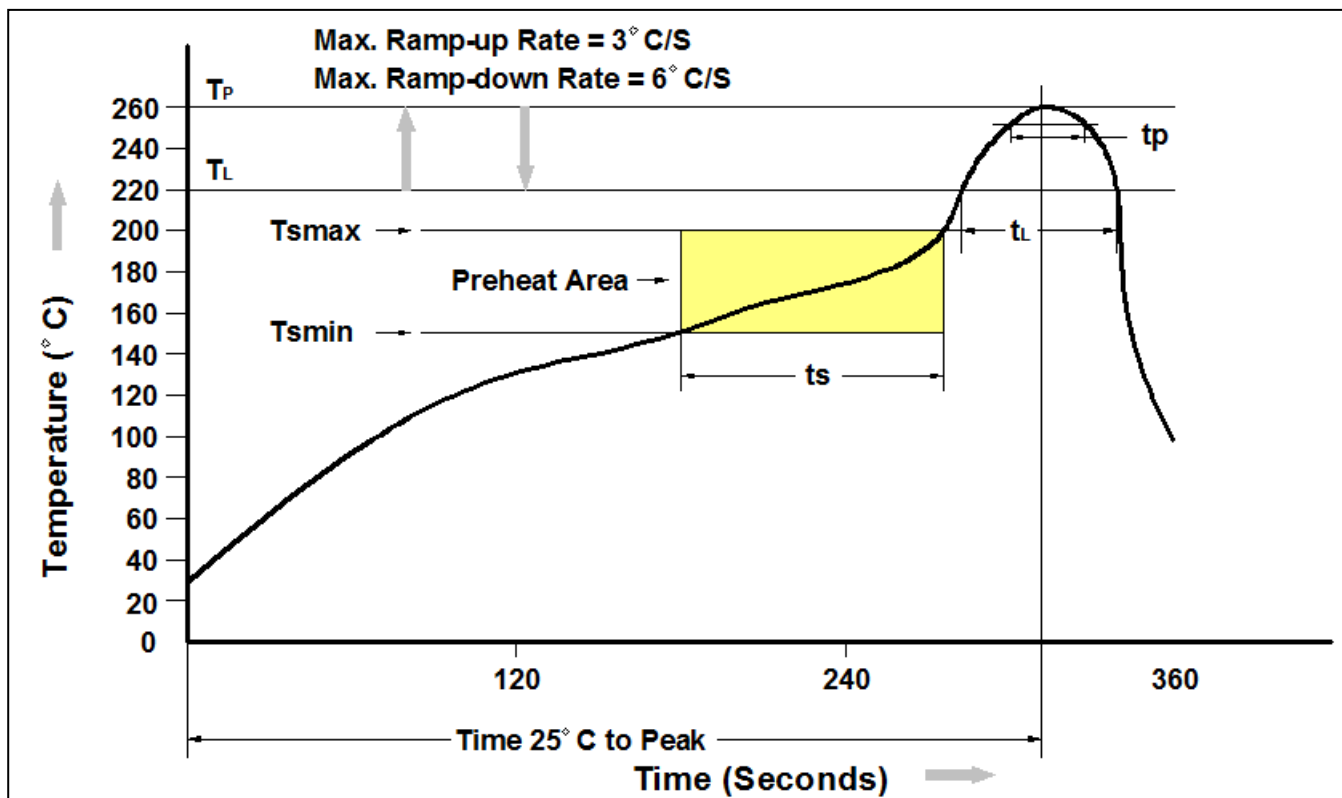
B605D : Device Number

Ordering Information

<i>Part Number</i>	<i>Description</i>	<i>Quantity</i>
CTLM16PS05-R3	SC-59 Reel	3000 pcs



Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{min})	150 °C
Temperature Max. (T _{max})	200 °C
Time (t _s) from (T _{min} to T _{max})	60-120 seconds
Ramp-up Rate (t _L to t _P)	3 °C/second max.
Liquidous Temperature (T _L)	217 °C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260 °C +0 °C / -5 °C
Time (t _P) within 5 °C of 260 °C	30 seconds
Ramp-down Rate (T _P to T _L)	6 °C/second max
Time 25 °C to Peak Temperature	8 minutes max.



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